Discontinued

P-Channel Silicon MOSFET

2SJ277



Ultrahigh-Speed Switching Applications

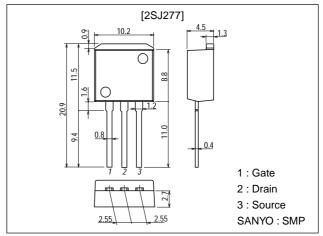
Features

- · Low ON resistance.
- · Ultrahigh-speed switching.
- · Low-voltage drive.
- · Surface mount type device making the following possible.
- · Reduction in the number of manufacturing processes for 2SJ277-applied equipment.
- · High density surface mount applications.
- · Small size of 2SJ277-applied equipment.

Package Dimensions

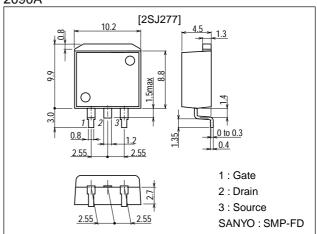
unit:mm

2093A



unit:mm

2090A



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Specifications

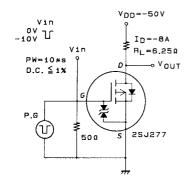
Absolute Maximum Ratings at Ta = 25°C

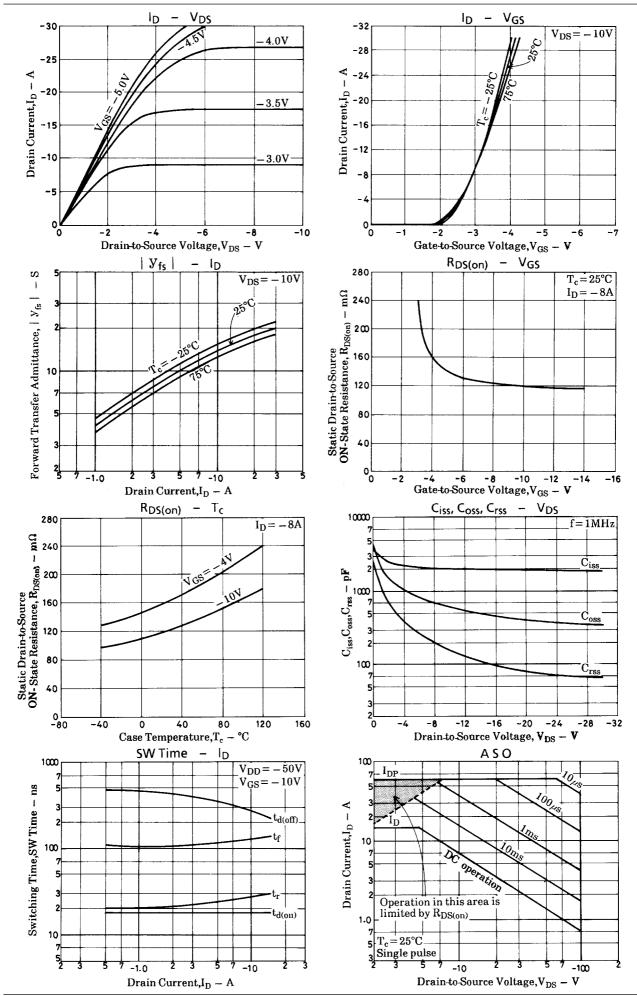
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-100	V
Gate-to-Source Voltage	VGSS		±15	V
Drain Current (DC)	ΙD		-15	Α
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-60	Α
Allowable Power Dissipation	PD		1.65	W
		Tc=25°C	70	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

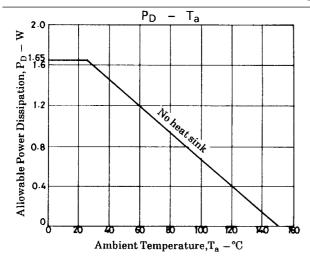
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0	-100			V
Gate-to-Source Breakdown Voltage	V _(BR) GSS	I _G =±100μA, V _{DS} =0	±15			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-100V, V _{GS} =0			-100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±12V, V _{DS} =0			±10	μΑ
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.0		-2.0	V
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-8A	7.5	13		S
Static Drain-to-Source ON-State Resistance	R _{DS(on)}	I _D =-8A, V _{GS} =-10V		120	160	mΩ
	R _{DS(on)}	I _D =-8A, V _{GS} =-4V		160	220	mΩ
Input Capacitance	Ciss	V _{DS} =–20V, f=1MHz		1900		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		400		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-20V, f=1MHz		80		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		18		ns
Rise Time	t _r	See specified Test Circuit		25		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		300		ns
Fall Time	t _f	See specified Test Circuit		120		ns
Diode Forward Voltage	V _{SD}	I _S =-15A, V _{GS} =0		-1.0	-1.5	V

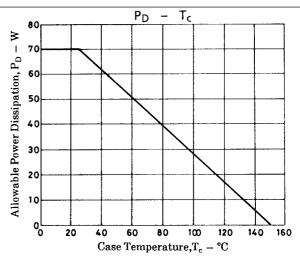
Switching Time Test Circuit





2SJ277





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